

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A thin film transistor substrate with a circuit repair feature in a liquid crystal display, the substrate comprising:

pixel electrodes;

data lines adjacent to each of two opposed sides of the pixel electrodes for applying data signals to the pixel electrodes via thin film transistors on the substrate;

gate lines disposed substantially perpendicular to said data lines for applying gate signals to the thin film transistors; and

~~gate dummy patterns parallel to said data lines adjacent to each of two opposed sides of the pixel electrodes and extending substantially the entire length of the pixel electrode portions adjacent and parallel to the data lines to overlap with at least one edge portion of said data lines and an edge portion of the pixel electrodes;~~

a plurality of gate dummy patterns,

wherein a first gate dummy pattern is located beneath only one side of a data line and running parallel to the data line and also located below only one side of a pixel electrode that is located adjacent to the one side of the data line, a second gate dummy pattern is located beneath only the other side of the data line and running parallel to the data line and also located below only one side of a pixel electrode that is located adjacent to the other side of the data line, the first and second gate dummy patterns being spaced from one another along their length, and

wherein the gate dummy patterns are physically located separate and apart from the gate lines

2. (Canceled)

3. (Previously Presented) The thin film transistor substrate according to claim 1, wherein when a data line is broken, a gate dummy pattern is used as a redundancy electrode for electrically connecting said broken data line.

4. (Currently Amended) The thin film transistor substrate according to claim 3, wherein ~~said~~ at least one gate dummy pattern includes a recess formed to permit a repair by disconnection of said gate dummy pattern from said gate line.

5. (Previously Presented) The thin film transistor substrate according to claim 1, wherein at least one gate dummy pattern is used as a black matrix.

6. (Previously Presented) The thin film transistor substrate according to claim 1, further comprising:

a storage capacitor defined by an overlapping part between at least one gate line and at least one pixel electrode.

7. (Previously Presented) The thin film transistor substrate according to claim 4, further comprising:

a protrusion protruded from at least one data line formed in such a manner as to overlap with said recess, thereby shutting off a light leaked between at least one gate dummy pattern and at least one gate line.

8. (Previously Presented) The thin film transistor substrate according to claim 1, wherein a gate-insulating layer is formed between at least one gate dummy pattern and at least one data line.

9. (Previously Presented) The thin film transistor substrate according to claim 4, wherein said recess is provided at a cutting part for breaking said gate dummy pattern from said gate line in such a manner that said recess is not overlapped with said broken data line.

10. (Currently Amended) ~~A~~ The thin film transistor substrate with a circuit repair feature in a liquid crystal display of claim 1, ~~said substrate comprising:~~

~~a pixel electrodes for driving a liquid crystal cells;~~
~~a data lines adjacent to each of two opposed sides of the pixel electrode for applying a data signal to said pixel electrode via a thin film transistors on the substrate;~~
~~a gate lines disposed substantially perpendicular to said data line for applying a gate signal to the thin film transistors; and~~

wherein gate dummy patterns parallel to said data lines adjacent to each of two opposed sides of the pixel electrodes and extending substantially the entire length of the pixel electrode portions adjacent and parallel to the data lines to overlap by about 0.5-1 μm with an edge portion of said data lines and an edge portion of said pixel electrodes, to thereby serve as a black matrix to shut off light leaked between said data lines and said pixel electrodes;

~~wherein the gate dummy patterns are physically located separate and apart from the gate lines.~~

11-20. (Canceled).

21. (Previously Presented) The thin film transistor substrate according to claim 1, wherein said gate dummy patterns are formed to cover substantially all of a gap between at least one of the edge portions of said data lines and an edge portion of said pixel electrodes.

22. (Previously Presented) The thin film transistor substrate according to claim 6, wherein an overlap portion of at least one gate dummy pattern and an edge portion of at least one pixel electrode with a gate insulating layer therebetween, forms an auxiliary storage capacitor.

23. (Previously Presented) The thin film transistor substrate according to claim 10, wherein said gate dummy patterns are formed to cover substantially all of a gap between at least one of the edge portions of said data lines and an edge portion of said pixel electrodes.

24-28. (Canceled)